

ABSTRACT

SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SEMICONDUCTOR DEVICE

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The present disclosure relates to a semiconductor device and a method of manufacturing the semiconductor device. The semiconductor device includes a stack structure including a plurality of interlayer insulating layers and a plurality of gate
10 conductive layers that are alternately stacked, a channel plug at least partially passing through the stack structure on a cell region, and a plurality of support structures at least partially passing through the stack structure on a contact region.

15 FIG. 3C